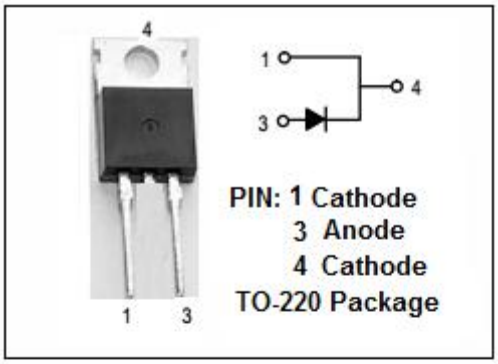
Schottky Barrier Rectifier — MBR8150

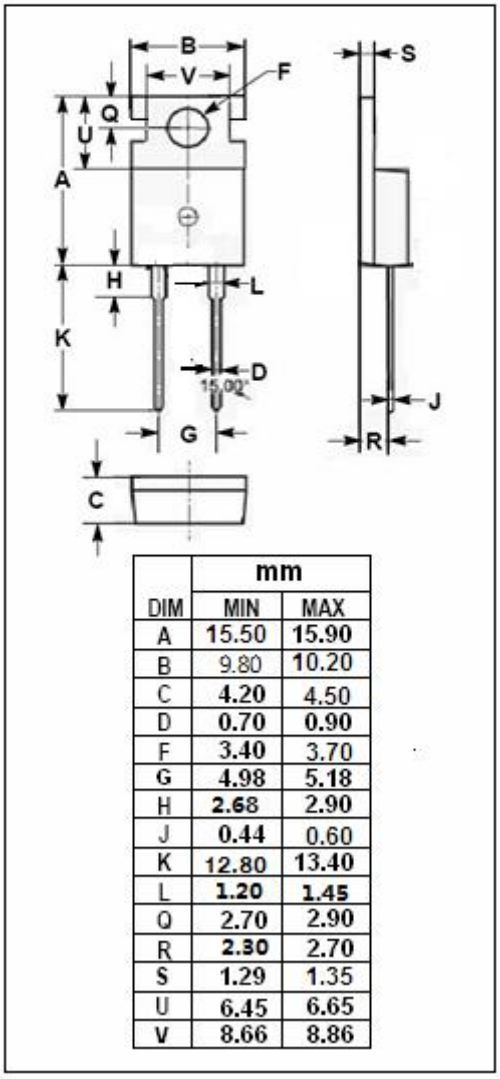


FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss/High Efficiency
- High Surge Capability
- High Current Capability，Low Forward Voltage Drop
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low-voltage,high frequency inverters，free wheeling and polarrity protection applications .



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RWM} V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	150	V
$V_{R(RMS)}$	RMS Reverse Voltage	105	V
$I_{F(AV)}$	Average Rectified Forward Current (Rated V_R) T_C= 125℃	8	A
I_{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	150	A
T_J	Junction Temperature	-65~175	℃
T_{stg}	Storage Temperature Range	-65~175	℃

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.0	℃/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300μs,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F= 8A ; T_C= 25℃	0.9	V
I_R	Maximum Instantaneous Reverse Current	Rated DC Voltage, T_C= 25℃ Rated DC Voltage, T_C= 125℃	0.05 20	mA